

**DAN209S  
DAP209S**

**DAN215  
DAP215**

**Diode, array, high-speed switching, leaded**

In these single packages, there are two diodes as shown in the circuit diagrams. They are available in different small envelopes.

#### Features

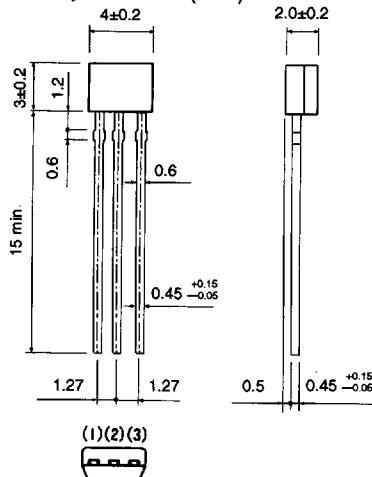
- available in SPT and FTL packages
- suitable for automatic mounting on printed circuit board
- all diodes in the package have similar characteristics

#### Applications

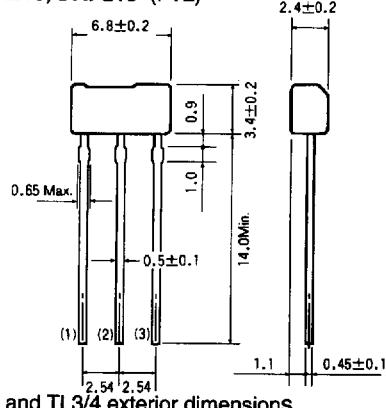
- high-speed switching

#### Dimensions (Units : mm)

**DAN209S, DAP209S (SPT)**

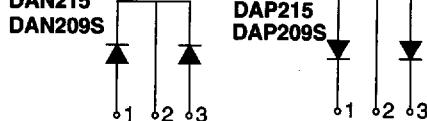


**DAN215, DAP215 (FTL)**



FTL and TL3/4 exterior dimensions

#### Equivalent circuits



**Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )**

Part no.	Peak reverse voltage $V_{RM}$ (V)	DC reverse voltage $V_R$ (V)	Peak forward current $I_F$ (mA)	Mean rectifying current $I_O$ (mA)	Surge current (1μs) $I_{surge}$ (A)	Power dissipation (Total) $P_d$ (mW)	Junction temp. $T_j$ (°C)	Storage temp. $T_{stg}$ (°C)
DAN209S	80	80	300	100	4	200	150	-55 ~ +150
DAP209S	80	80	300	100	4	200	150	-55 ~ +150
DAN215	80	80	300	100	4	200	150	-55 ~ +150
DAP215	80	80	300	100	4	200	150	-55 ~ +150

**Electrical characteristics (unless otherwise noted,  $T_a = 25^\circ\text{C}$ )**

Part no.	Forward voltage		Reverse current		Capacitance between terminals			Reverse recovery time			
	$V_F$ (V) Max	$I_F$ (mA) Max	$I_R$ (μA) Max	$V_R$ (V)	$C_T$ (pF) max.	$V_R$ (V)	f (MHz)	$t_{rr}$ (ns) Max	$V_R$ (V)	$I_F$ (mA)	Ref
DAN209S	1.2	100	0.1	70	3.5	6	1	4	4	6	Figure 8
DAP209S	1.2	100	0.1	70	3.5	6	1	4	4	6	Figure 8
DAN215	1.2	100	0.1	70	3.5	6	1	4	4	6	Figure 8
DAP215	1.2	100	0.1	70	3.5	6	1	4	4	6	Figure 8

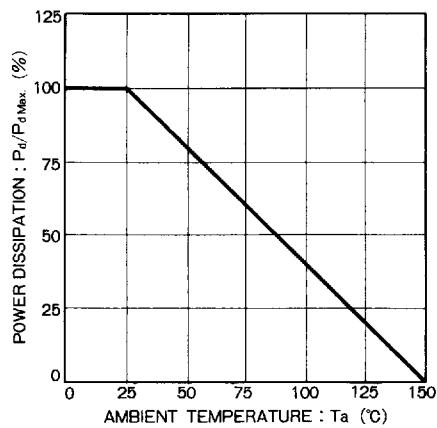
**Electrical characteristic curves**

Figure 1

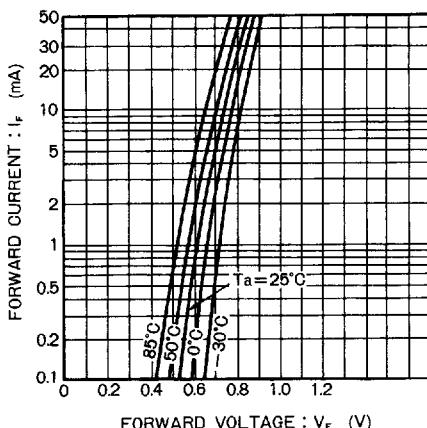


Figure 2

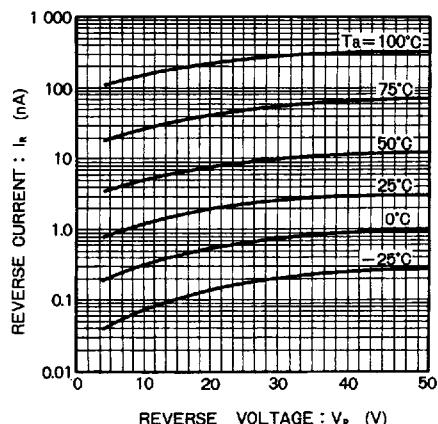


Figure 3

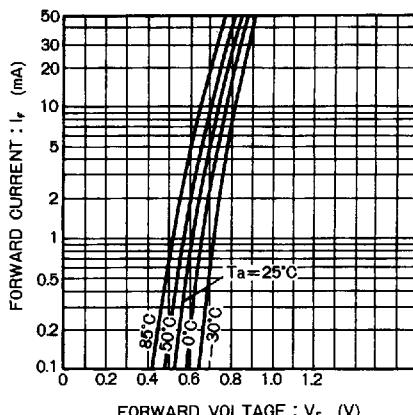


Figure 4

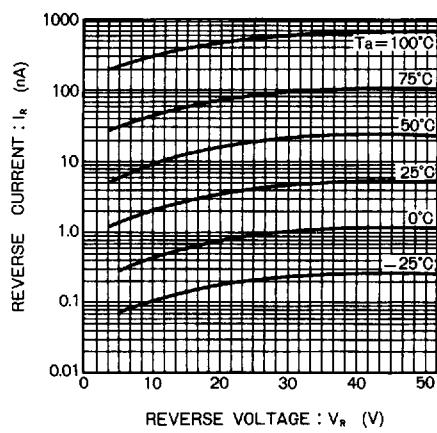


Figure 5

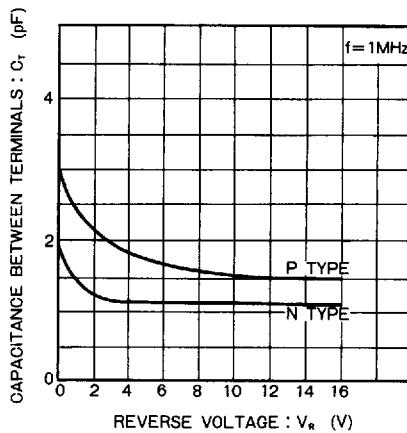


Figure 6

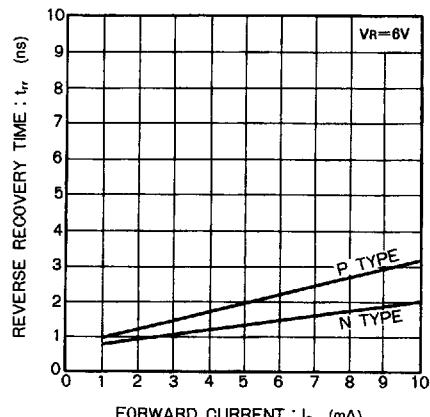
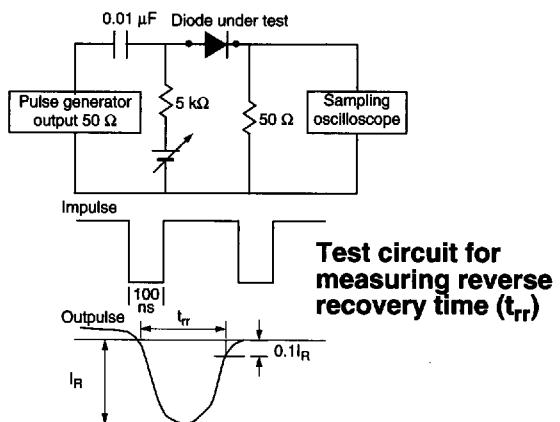


Figure 7



Test circuit for measuring reverse recovery time ( $t_{rr}$ )